P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
- 20	0.051 at V_{GS} = - 4.5 V	- 5.1
	0.067 at V_{GS} = - 3.3 V	- 4.5
	0.100 at V_{GS} = - 2.5 V	- 3.7

FEATURES

- TrenchFET® Power MOSFET
- PWM Optimized

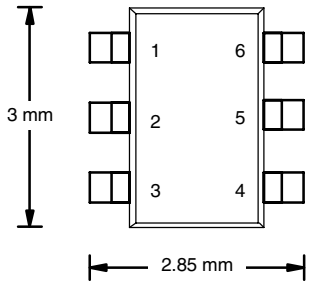
Pb-free Available

RoHS* COMPLIANT

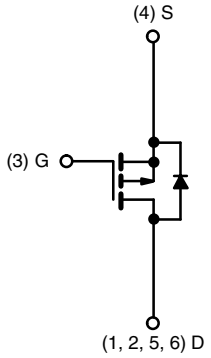
APPLICATIONS

- DC/DC
  - HDD
  - Power Supplies
- Portable Devices Such As Cell Phones, PDA, DSC, and DVC

TSOP-6
Top View



Ordering Information: Si3867DV-T1
Si3867DV-T1-E3 (Lead (Pb)-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted					
Parameter		**Symbol**	**5 sec**	**Steady State**	**Unit**
Drain-Source Voltage		V_{DS}	- 20		V
Gate-Source Voltage		V_{GS}	± 12		
Continuous Drain Current (T_J = 150 °C)[a]	T_A = 25 °C	I_D	- 5.1	- 3.9	A
	T_A = 85 °C		- 3.7	- 2.8	
Pulsed Drain Current		I_{DM}	- 20		
Continuous Diode Current (Diode Conduction)[a]		I_S	- 1.7	- 0.9	
Maximum Power Dissipation[a]	T_A = 25 °C	P_D	2.0	1.1	W
	T_A = 85 °C		1.0	0.6	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[a]	t ≤ 5 sec	R_{thJA}	45	62.5	°C/W
	Steady State		90	110	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	25	30	

Notes:
a. Surface Mounted on 1" x 1" FR4 Board.

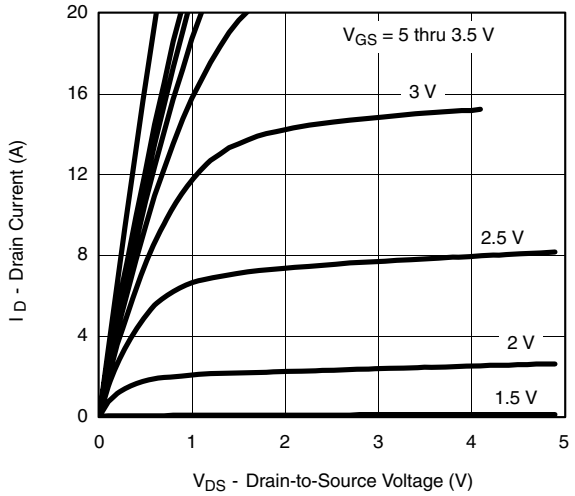
* Pb containing terminations are not RoHS compliant, exemptions may apply.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min**	**Typ**	**Max**	**Unit**
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 0.6		- 1.4	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 12 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 20 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 20 V, V_{GS} = 0 V, T_J = 85 °C			- 5	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = - 5 V, V_{GS} = - 4.5 V	- 20			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = - 4.5 V, I_D = - 5.1 A		0.041	0.051	Ω
		V_{GS} = - 3.3 V, I_D = - 4.5 A		0.054	0.067	
		V_{GS} = - 2.5 V, I_D = - 2 A		0.081	0.100	
Forward Transconductance[a]	g_{fs}	V_{DS} = - 5 V, I_D = - 5.1 A		11		S
Diode Forward Voltage[a]	V_{SD}	I_S = - 1.7 A, V_{GS} = 0 V		- 0.7	- 1.2	V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_D = - 5.1 A		7	11	nC
Gate-Source Charge	Q_{gs}			2.3		
Gate-Drain Charge	Q_{gd}			1.6		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 10 V, R_L = 10 Ω $I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_G = 6 Ω		17	30	ns
Rise Time	t_r			31	50	
Turn-Off Delay Time	$t_{d(off)}$			32	50	
Fall Time	t_f			30	50	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = - 1.7 A, di/dt = 100 A/µs		25	50	

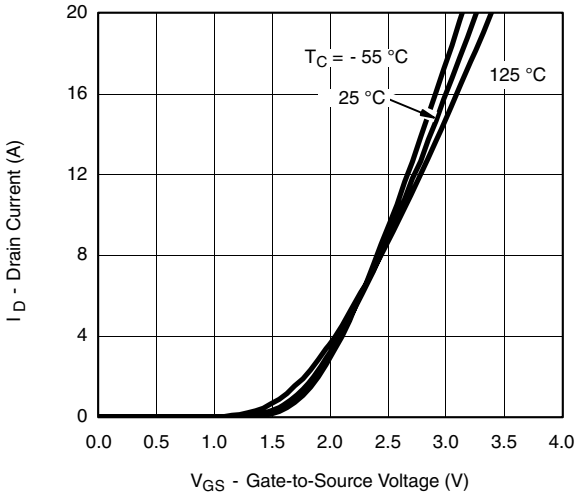
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C unless noted

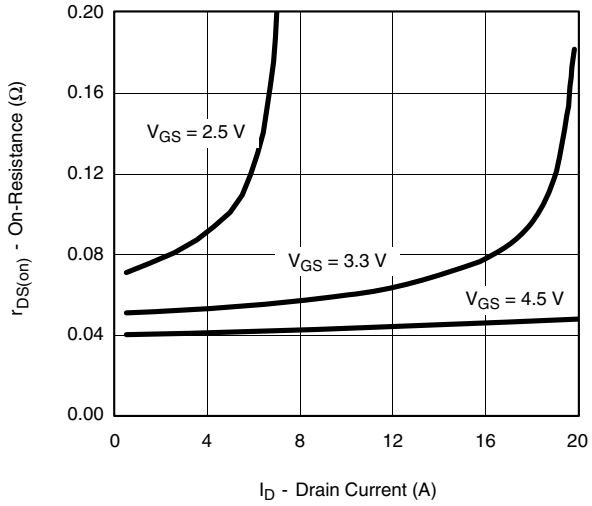


Output Characteristics

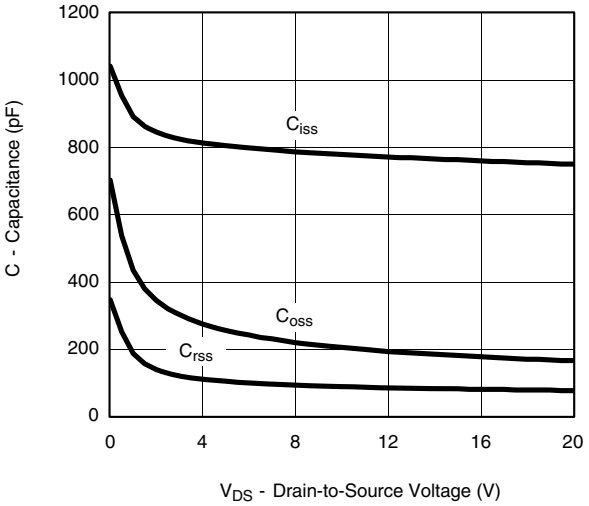


Transfer Characteristics

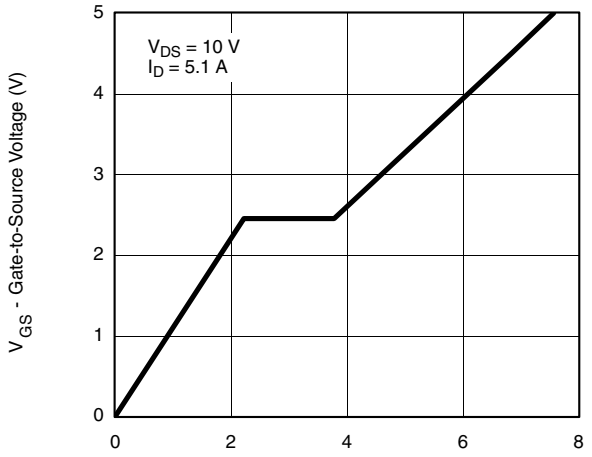
TYPICAL CHARACTERISTICS 25 °C unless noted



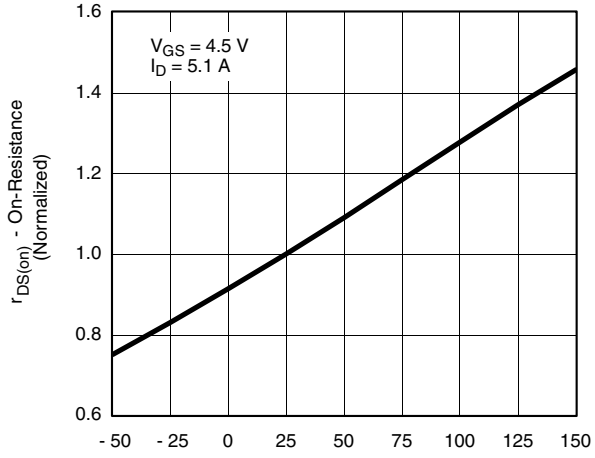
On-Resistance vs. Drain Current



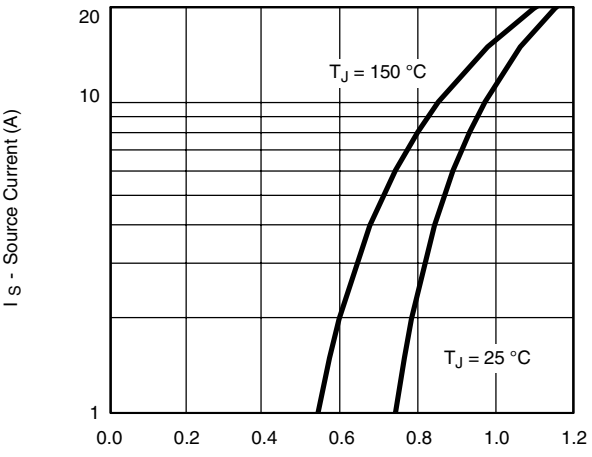
Capacitance



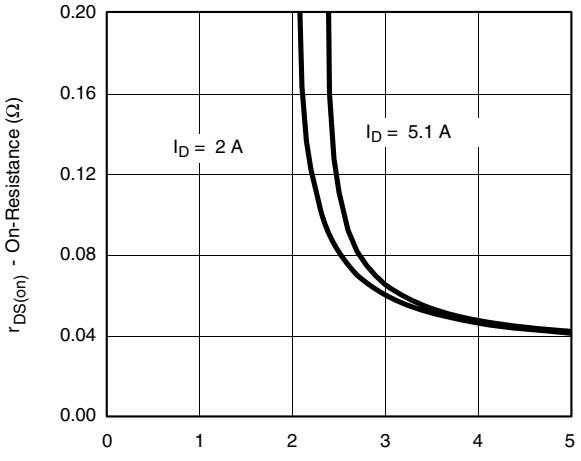
Gate Charge



On-Resistance vs. Junction Temperature

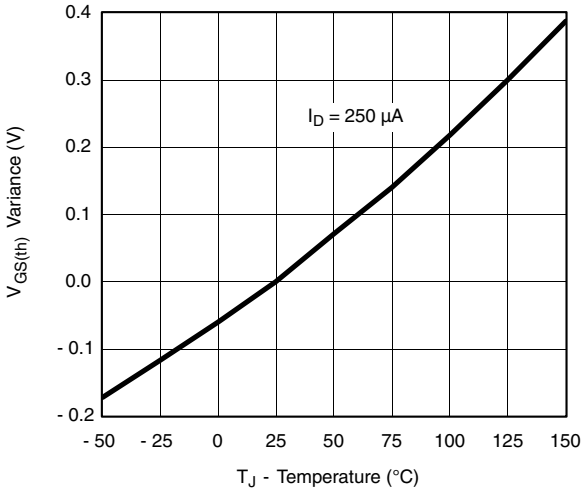


Source-Drain Diode Forward Voltage

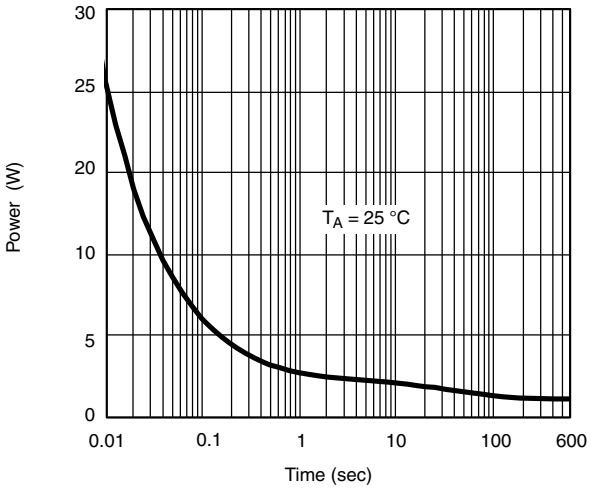


On-Resistance vs. Gate-to-Source Voltage

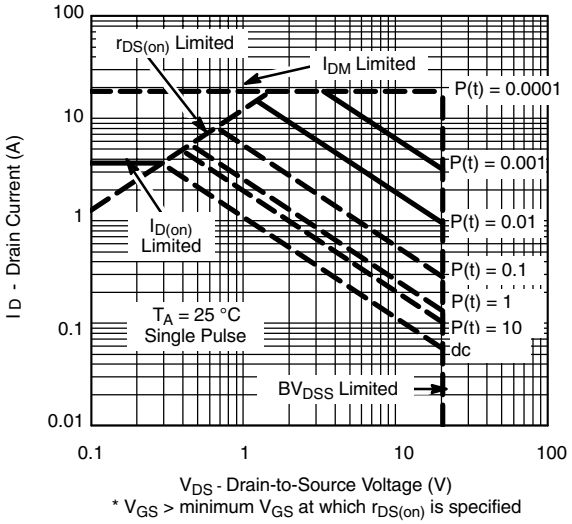
TYPICAL CHARACTERISTICS 25 °C unless noted



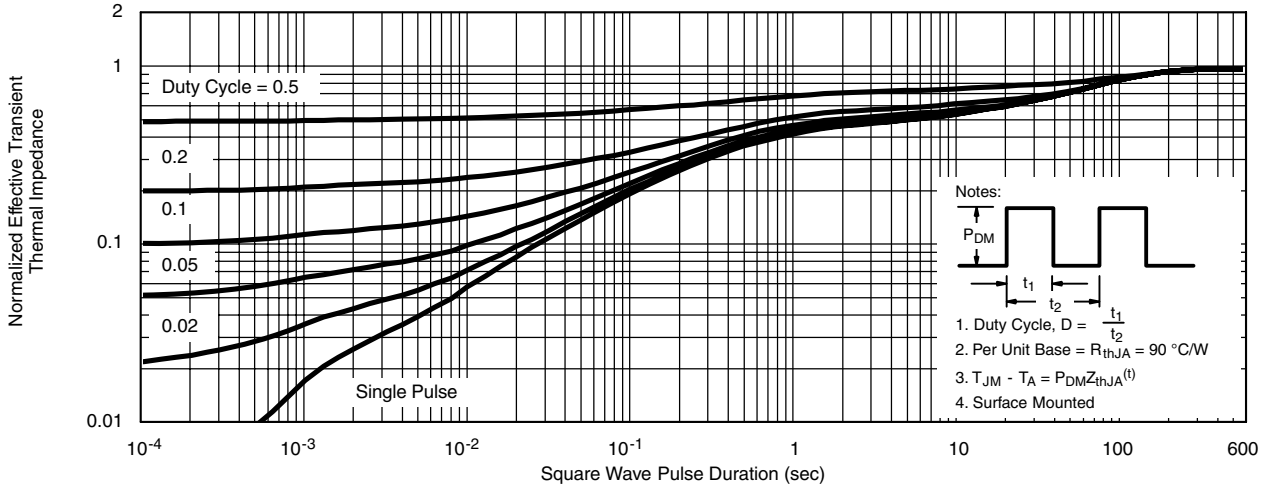
Threshold Voltage



Single Pulse Power

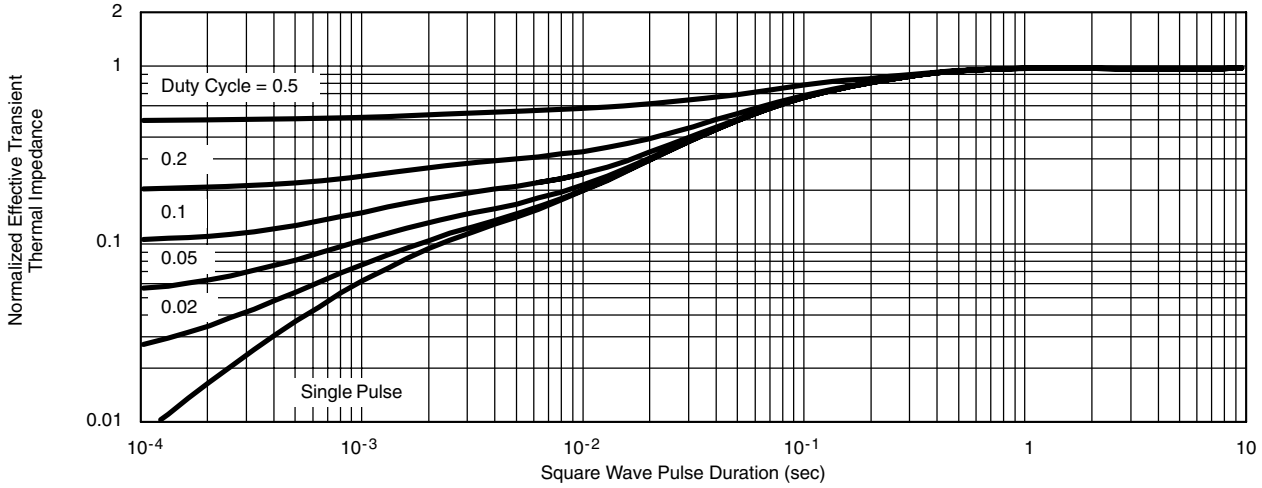


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C unless noted



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?72068.

Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, “Vishay”), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay’s terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.